

**Amendment to the Specification**

Replace the paragraph beginning on page 6 at line 11 with the following:

Referring to Fig. 1D, a titanium thin film 9' having a thickness of 300Å ( $10^{-8}$ cm) is superimposed again on the titanium silicide films 4s, 7s', 8s'. A heat treatment is then performed again in an N<sub>2</sub> atmosphere for ten seconds at 700°C by the RTA apparatus. Subsequently, the solution of ammonia and hydrogen peroxide is used to remove the titanium that did not react with ~~the titanium~~ the conductive portions 4, 7, 8. In this state, high resistance titanium silicide films that are made the C49 phase and are sufficiently thick are respectively formed on the surfaces of the gate electrode 4, the source section 7 and the drain section 8. Afterward, an additional heat treatment is performed in a nitrogen (N<sub>2</sub>) atmosphere for 30 seconds at 850°C by the RTA apparatus. Referring to Fig. 1E, this forms low resistance titanium silicide films 4s, 7s 8s, which are made of a C54 phase, on the surfaces of the gate electrodes 4, the source section 7, and the drain section.